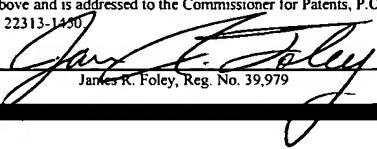


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James R. Foley, Reg. No. 39,979

**A NEW HARD BISR SCHEME CAPABLE OF DOING FIELD REPAIR
AND USAGE OF RELIABILITY CONTROLLER**

Inventors

Mukesh K. Puri
44978 Lynx Drive
Fremont, CA 94539

Ghasi R. Agrawal
1633 Canary Drive
Sunnyvale CA 94087

Tuan L. Phan
2483 Amaryl Drive
San Jose, CA 95132

Background of the Invention

The present invention relates to Built-In-Self Repair schemes and controllers for Built-In-Self Repair designs.

Built-in-Self-Repair (BISR) is a scheme wherein a certain amount of
5 redundant elements are provided in each memory so that random process defects do not cause excessive yield loss. As shown in Figure 1, current widely-used versions of BISR run different patterns at wafer-level to test the memories on the chip (box 10 in Figure 1) and generate a repair solution which can be scanned out of the chip (via the flarescan mode) and written to an output file (box 12 in Figure 1). The
10 repair solutions are then programmed on the respective devices by blowing fuses (box 14 in Figure 1). Thereafter, a power-on state machine (on-chip) repairs the memories (box 16 in Figure 1). The power-on state machine runs a BISR mode called fusescan which loads the fuse values into the memories. This repairs the memories (soft-repair) after which they can be accessed in the functional mode.

15 However, with the current hard-BISR scheme, once the fuses are blown, there is no ability to rerun the BISR and repair any new failures that might occur during the life-time of the device. The repair is constrained to the information stored in the fuses.

Generally, memory contents have been increasing, and memories have
20 higher defect densities than logic. As such, BISR is generally used in designs with large memory contents to repair defective memories. Parts which are repaired are prone to have higher reliability problems (DPM - defects per million). However, many companies which insist on certain reliability goals do not prefer to concede on DPM goals. Hence, it becomes necessary to screen these devices so as to reject the
25 ones that exceed a certain threshold of repair beyond which they might pose a reliability risk over the lifetime of that device. The existing method requires that

the repair solutions be logged to a file, and then post-processed to determine the extent of repair on each device and then screen out the ones that exceed a certain threshold. This takes time and often requires very extensive post-processing of data or maintaining complex production processes.

Objects and Summary

An object of an embodiment of the present invention is to provide a hard-BISR scheme which includes provisions for repairing field failures.

5 Another object of an embodiment of the present invention is to provide a scheme which uses an on-chip circuit to analyze amount of repair on a device and modes which allow for field repair even with hard-BISR.

Still another object of an embodiment of the present invention is to provide a scheme which saves test time by not data-logging devices which would be thrown out and saves production setup and turn-around time.

10 Yet another object of an embodiment of the present invention is to provide a scheme which allows for the selective use of redundant resources for different products and also for different technology.

Still yet another object of an embodiment of the present invention is to provide a scheme which allows memory assessment on the fly during wafer testing.

15 Briefly, and in accordance with at least one of the foregoing objects, an embodiment of the present invention provides a BISR scheme which provides for on-chip assessment of the amount of repair on a given memory and for the flagging of any device as a fail when the device exceeds a pre-determined limit. Preferably, a counter is built and loaded through a test pattern during production testing, and
20 the counter establishes the threshold for pass/fail criteria. The BISR is configured to load a repair solution and then test the memories for any additional failures and if there are any, repair them (provided enough redundant elements are available). In addition, a reliability controller for BISR designs can be provided, where the reliability controller contains a register set and a number of counters at the chip-
25 level which can be loaded through a test pattern during production tests, where one of the counters contains the number of memories to be allowed for repair.

Brief Description of the Drawings

The organization and manner of the structure and operation of the invention, together with further objects and advantages thereof, may best be understood by reference to the following description, taken in connection with the accompanying drawing, wherein:

Figure 1 illustrates a prior art BISR scheme;

Figure 2 illustrates a BISR scheme which is in accordance with an embodiment of the present invention; and

Figure 3 illustrates a reliability controller for BISR designs, where the reliability controller is in accordance with another embodiment of the present invention.

Description

While the invention may be susceptible to embodiment in different forms, there are shown in the drawings, and herein will be described in detail, specific embodiments with the understanding that the present disclosure is to be considered
5 an exemplification of the principles of the invention, and is not intended to limit the invention to that as illustrated and described herein.

As discussed above, with the hard-BISR scheme which is currently widely-used (see Figure 1), once the fuses are blown, there is no ability to rerun the BISR and repair any new failures that might occur during the life-time of the device. The
10 repair is constrained to the information stored in the fuses. Some field Repair scheme has been suggested. However, it does not make certain that some redundant elements are available in the field for extra field repair (not used in the factory). As shown in Figure 2, an embodiment of the present invention provides a hard-BISR scheme which includes provisions for repairing field failures. The BISR scheme
15 provides for on-chip assessment of the amount of repair on a given memory and for the flagging of any device as a fail when the device exceeds a pre-determined limit. Preferably, a counter is built and loaded through a test pattern during production testing, and the counter establishes the threshold for pass/fail criteria. The BISR is configured to load a repair solution and then test the memories for any additional
20 failures and if there are any, repair them (provided enough redundant elements are available).

The BISR scheme can be implemented by effecting two modifications to an existing BISR:

- a. Modify the repair information scan mode so as to ensure that every repairable device still has some unused redundant elements available for field repair. An efficient way of implementing this is to make the assessment on the fly during wafer testing itself. It reduces the test time and does not require very extensive post-processing of data or maintaining complex production processes. That means that the repair information scan mode needs to be modified so as to be able to make an on-chip assessment of the amount of repair on a given memory and flag any device as a fail when it exceeds a certain limit. However, since this repair limit may vary across technologies and products, it cannot be hard-wired in the BISR scheme itself but rather needs to be a variable entity. One possible way of doing that is to build a counter as part of BISR which can be loaded through a test pattern during production testing that would establish threshold for pass/fail criteria (box 20 in Figure 2).
- b. Modify the functionality of the power-on state machine so that it runs BISR accumulate mode after doing fuse scan. In such a case, Fuse scan loads the factory computed repair solution, and then the BISR accumulate mode tests the memories for any additional failures and if there are any, repair them (provided enough redundant elements are available) (box 22 in Figure 2).

Such an embodiment provides a scheme which uses an on-chip circuit to analyze amount of repair on a device and modes which allow for field repair even with hard-BISR. This saves test time by not data-logging devices which would be thrown out and saves production setup and turn-around time. Moreover, the scheme allows for the control of use of redundant resources for different products and also for different technology. In addition, the use of redundant resources can be controlled to any value for the same product over the lifetime, i.e., for a product, less or more resources can be allowed at different times depending on the maturity of the process and reliability (Defects Per Million) required. The part of the scheme can also be used for soft BISR scheme where the amount of redundant element usage can be restricted to a certain amount, so that some additional field repair which may be necessary because of Early Failure Rate (EFR) or some other reasons.

Figure 3 illustrates a reliability controller 30 for BISR designs, where the reliability controller 30 is in accordance with another embodiment of the present invention. The reliability controller 30 is configured to assess the number of repairable memories on the fly during wafer testing itself. It reduces the test time and does not require very extensive post-processing of data or maintaining complex production processes. That means that an on-chip assessment of the absolute amount of repairable memory needs to be done and any device which exceeds a certain limit needs to be flagged. However, since this repair limit may vary across technologies and in some cases across products, it cannot be hard-wired in the BISR scheme itself but rather needs to be a variable entity which may be varied from device to device. One possible way of doing that is to build a reliability controller 30 as shown in Figure 3 which contains a Register set 32 and number of counters 34, 36 at the chip-level which can be loaded through a test pattern during

production tests. One counter 34 (counter 1) contains the number of memories to be allowed for repair.

Figure 3 also shows an example of how this logic is connected to the BISR Systems 40 at chip-level. The controller 30 contains two counters 34, 36, a set of registers 32 and some logic 38. The connection of the controller needs to be done to the logic 38 which scans out the repair information via flarescanout pins 42 from BISR system 40. (Figure 3 shows an example of how repair information gets scanned out using global flare register 44. However, many companies do the scan out of repair information using Tap Controller 46 or through some other methods, and the basic idea of the reliability controller to be used with these types of logic remains the same for all kinds of implementations).

Counter 1 (34) contains a value which indicates the total number of repairable memories. This value gets loaded through the pattern. At the same time, two numbers are loaded in the register set 32 -- one indicates the total number of BISR memories in the design, and the other contains the maximum number of flare register bits among these memories. The logic 38 uses these two numbers to load another counter -- counter 2 (36) -- to create sections of patterns for each memory. The start of each section contains the redundant element usage information. Logic based on the counter 2 value is configured to get to the start of each section in the pattern and get the redundant element usage information.

Typically, the repair information contains some bits which will be "1" if redundant element is/are being used. The repair information also contains other information bits (for example, defective elements, number of defects etc.). The logic 38 within the reliability controller 30 reads the redundant element usage information and if it sees a "1" then it decrements the counter 1 value. Based on the number of repaired memories being allowed, the counter 1 reaches a value "0" if the

chip has more than allowed repairable memories and that is when a FLAG (unreliable) would go high indicating that the memory is potentially unreliable and should be rejected.

The number of flare register bits can be different for different memories.

5 However, logic (something similar to Global Flare Reg) can be utilized to normalize the length of the flare registers using patterns.

Figure 3 illustrates an on-chip circuit to analyze the amount of repair required and flag the device as a failure if it exceeds pre-set limits. Moreover, the amount of repairable memories can be varied from design to design (based on the
10 number of memories in the designs) and also for various technologies. At the same time, the same can be controlled at various times during the lifetime of the product. The method saves test time by not data-logging devices which would be thrown out and saves production setup and turn-around time.

While embodiments of the present invention are shown and described, it is
15 envisioned that those skilled in the art may devise various modifications of the present invention without departing from the spirit and scope of the appended claims.